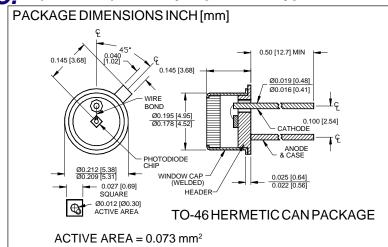
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive (MRD 510) Industry Equivalent Type PDB-C120 DETECTORS INC.





FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The PDB-C120 is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a flat window.

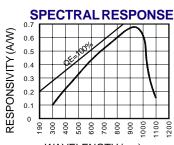
APPLICATIONS

- Fiber optic
- Laser detection
- Light demodulation
- Matched to I.R. LEDs

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_{BR}	Reverse Voltage		200	V
T _{STG}	Storage Temperature	-65	+150	∘C
T _o	Operating Temperature Range	-55	+125	∘C
T _s	Soldering Temperature*		+240	∘C
I _L	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

(171-25 C dilloco callollinos fictor)								
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS		
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	1.2	1.5		μ A		
I _D	Dark Current	H = 0, V _R = 10 V		0.5	2.0	nA		
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	400	500		MΩ		
TCR _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/°C		
C _J	Junction Capacitance	H = 0, V _R = 10 V**		1		pF		
λrange	Spectral Application Range	Spot Scan	350		1100	nm		
λр	Spectral Response - Peak	Spot Scan		950		nm		
V _{BR}	Breakdown Voltage	I = 10 μA	100	150		V		
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		9.0x10 ⁻¹⁵		W/ √Hz		
tr	Response Time	RL = 1 KΩ V _p = 50 V		1.0		nS		